

# AZ 6100 系列光刻胶

## 高感光度高热稳定性G线正型光刻胶

广泛应用于大规模集成电路的高感光度高热稳定性G线正型光刻胶

### 特征

- 1) 通过提高光刻胶的热稳定性, 从而改善了干法刻蚀的工艺窗口
- 2) 高感光度带来了高产出率
- 3) 很宽的膜厚范围

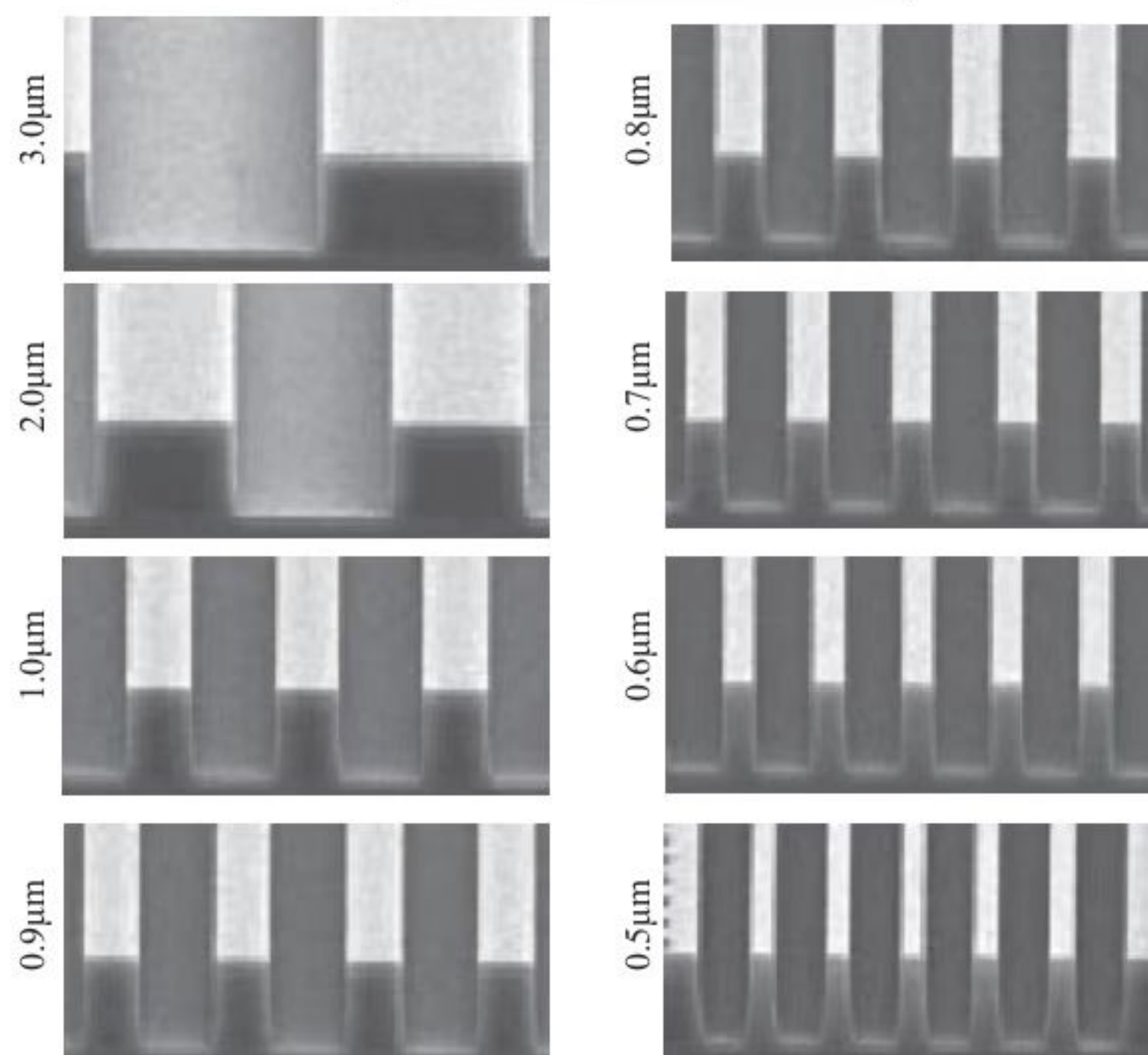
### 参考工艺条件

前烘	: 100°C 60秒 (DHP)
曝光	: G线步进式曝光机/接触式曝光机
显影	: AZ300MIF (2.38%) 23°C 60秒 Puddle
清洗	: 去离子水30秒
后烘	: 120°C 120秒 (DHP)
剥离	: AZ剥离液及/或氧等离子体灰化

### 产品型号(PRODUCT RANGE)

Product Name	AZ6112	AZ6124	AZ6130
Viscosity	13mPa	43mPa	69mPa

### 解像度(Resolution)



### Process Condition

Substrate	: Bare-Si 4" wafer
Film Thickness	: 1.3µm
Pre-bake	: 100°C 90sec.(DHP)
Exposure	: g-line Stepper(NA=0.54) 110msec.
Developing	: AZ 300MIF Developer(2.38%) 23°C 60sec.

## High Sensitivity & High Heat Stability g-line Positive-tone Photoresist

High sensitivity & high heat stability g-line positive-tone photoresist for general purpose~semi-critical process

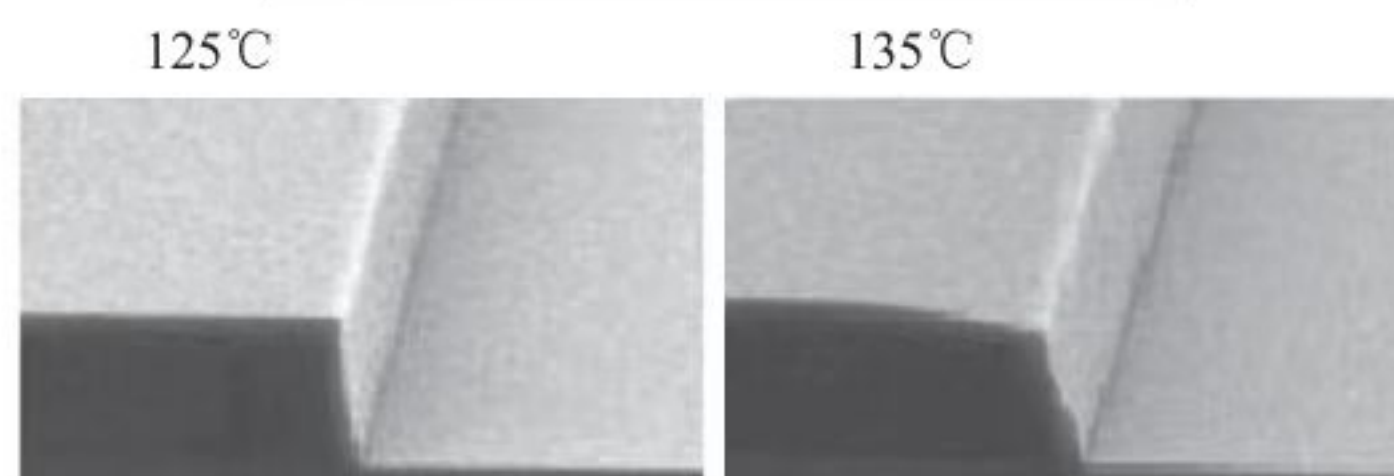
### FEATURES

- 1) Improvement of dry etching process margin by high heat stability
- 2) Achievement of high throughput by high sensitivity
- 3) Wide viscosity variation

### SAMPLE PROCESS CONDITIONS

Pre-bake	: 100°C 60sec.(DHP)
Exposure	: g-line stepper and/or Contact Aligner
Developing	: AZ300MIF (2.38%) 23°C 60sec.Puddle
Rinse	: DI-water 30sec.
Post-bake	: 120°C 120sec.(DHP)
Stripping	: AZ Remover and/or O <sub>2</sub> plasma-ashing

### 耐热性(Thermal Stability)



### Spin Curve

